

GS551 DATA SHEET

FEATURES

- adjustable gain to 48 dB
- · capable of driving low impedance receiver
- · low component count, 3 small capacitors and 1 resistor
- gain trim can be used as vol. control for reduced noise
- minimal start-up transient
- no gain expansion

STANDARD PACKAGING

- 10 pin MICROpac
- 10 pin PLID®
- 10 pin SLT
- Chip (68 x 60 mils)

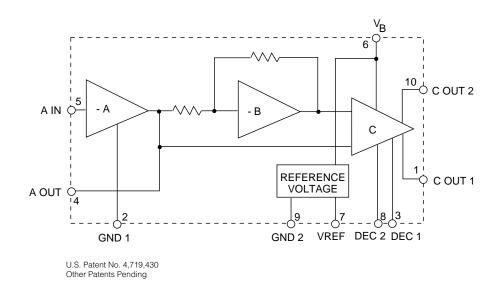
Au Bump

CIRCUIT DESCRIPTION

The GS551 is a 10 pin, low voltage, class B amplifier which operates over a battery range of 1.1 VDC to 3 VDC.

The GS551 consists of three gain blocks. The first block is an inverting amplifier with the gain set by two external resistors. The gain trim feature can be used as a volume control in hearing aid applications. The second block is an inverting unity gain amplifier which serves as a phase splitter. The outputs from the first and second blocks drive the differential input of the third block. The third block has a fixed AC gain of 28 dB when driving a receiver.

The amplifier has internal compensation eliminating the need for a capacitor across the receiver. Two ground pins are available for "Star" grounding to reduce any second order harmonic distortion introduced by ground line resistance.



BLOCK DIAGRAM

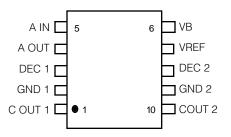
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ABSOLUTE MAXIMUM RATINGS

PIN CONNECTION

PARAMETER	VALUE/UNITS			
Supply Voltage	5 VDC			
Operating Temperature	-10 to +40 °C			
Storage Temperature	-20 to +70 °C			
CAUTION CLASS 1 ESD SENSITIVITY	R			



ELECTRICAL CHARACTERISTICS

Conditions: Frequency = 1 kHz, Temperature = 25°C, Supply Voltage V_{B} = 1.3 VDC

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
Gain	A _V	V _o =0.707 VRMS	46	48	50	dB
Amplifier Current	I _{AMP}		120	220	335	μA
Transducer Current	I _{trans}		120	250	390	μA
Input Referred Noise	IRN	NFB 0.2 to 10 kHz at 12 dB/Oct	-	1.3	2.5	μV
Total Harmonic Distortion THD	тнр	V _o =0.707 VRMS	-	0.25	1.3	%
		V ₀ =1.3 VRMS	-	0.3	1.5	%
Stable with R _B to	R _{STAB}	$R_B = 22\Omega$	-	-	22	Ω
Maximum Output Current	I _{OUT}	V _{P8} =0	-	>35	-	mA

All parameters remain as shown in Test Circuit unless otherwise stated in "Conditions" column

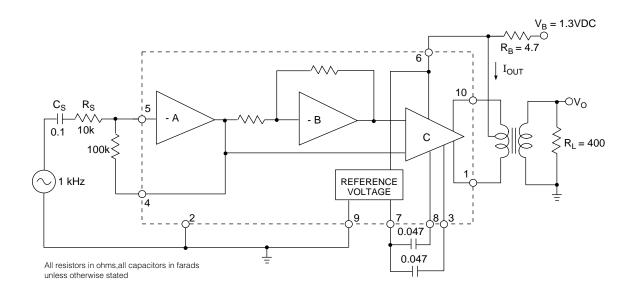
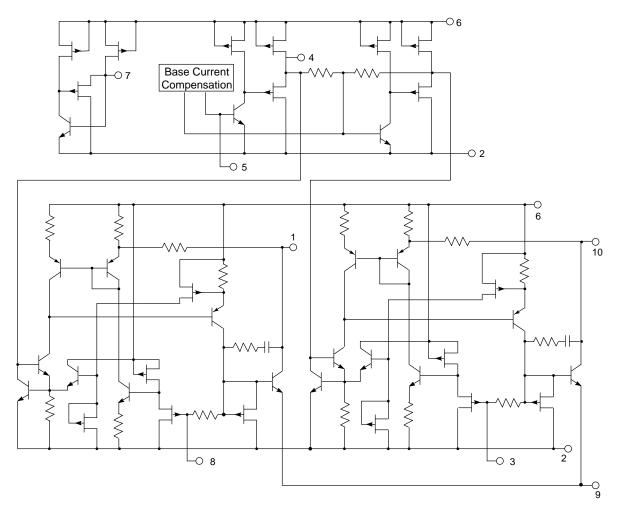


Fig. 1 Test Circuit





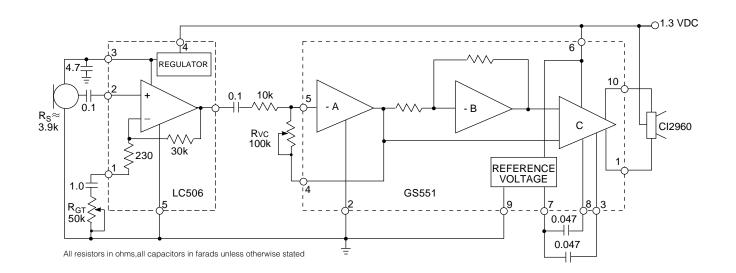
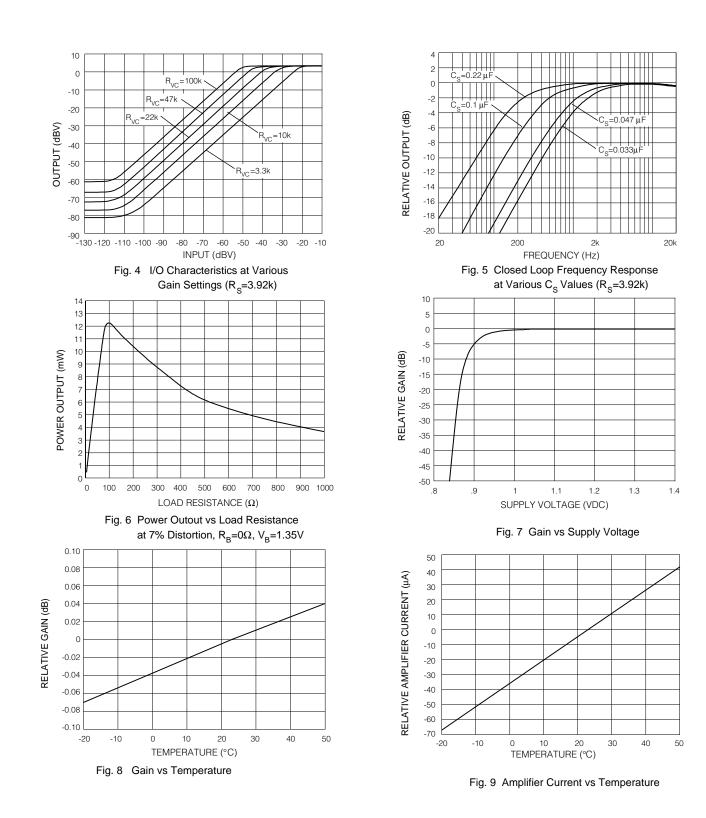


Fig. 3 Application Circuit



REVISION NOTES: Pb/Sn bump removed, V_{P8}=0 added to Electrical Characteristics, I_{OUT} added to Test Circuit

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